

Dual Switching Diode Common Anode

BAW56L, SBAW56L

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (EACH DIODE)

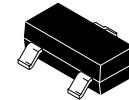
Rating	Symbol	Value	Unit
Reverse Voltage	V _R	70	V
Forward Current	I _F	200	mA
Forward Surge Current (60 Hz @ 1 cycle)	I _{FSM}	2.0	A
Non-Repetitive Peak Forward Current t = 1 μ s (Note 3)	I _{FSM}	4.0	A
Repetitive Peak Forward Current Pulse Wave = 1 sec, Duty Cycle = 66%	I _{FRM}	500	mA
ESD Rating: Human Body Model Machine Model Charged Device Model	ESD	Class 3A Class M4 Class C3	

THERMAL CHARACTERISTICS

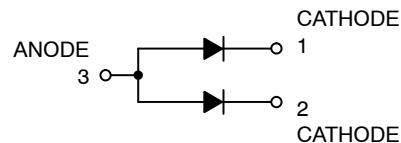
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R _{θJA}	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R _{θJA}	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

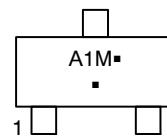
1. FR-5 = 1.0 × 0.75 × 0.062 in.
2. Alumina = 0.4 × 0.3 × 0.024 in. 99.5% alumina.
3. Square Wave; T_J = 25°C.



SOT-23 (TO-236)
CASE 318
STYLE 12



MARKING DIAGRAM



A1 = Device Code

M = Date Code*

▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
BAW56LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SBAW56LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
BAW56LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
SBAW56LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

BAW56L, SBAW56L

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Each Diode)

Characteristic	Symbol	Min	Max	Unit
Reverse Breakdown Voltage ($I_{(BR)} = 100 \mu\text{A}$)	$V_{(\text{BR})}$	70	–	V
Reverse Voltage Leakage Current ($V_R = 25 \text{ V}, T_J = 150^\circ\text{C}$) ($V_R = 70 \text{ V}$) ($V_R = 70 \text{ V}, T_J = 150^\circ\text{C}$)	I_R	– – –	30 2.5 50	μA
Diode Capacitance ($V_R = 0 \text{ V}, f = 1.0 \text{ MHz}$)	C_D	–	2.0	pF
Forward Voltage ($I_F = 1.0 \text{ mA}$) ($I_F = 10 \text{ mA}$) ($I_F = 50 \text{ mA}$) ($I_F = 150 \text{ mA}$)	V_F	– – – –	715 855 1000 1250	mV
Reverse Recovery Time ($I_F = I_R = 10 \text{ mA}, I_{R(\text{REC})} = 1.0 \text{ mA}$) (Figure 1) $R_L = 100 \Omega$	t_{rr}	–	6.0	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

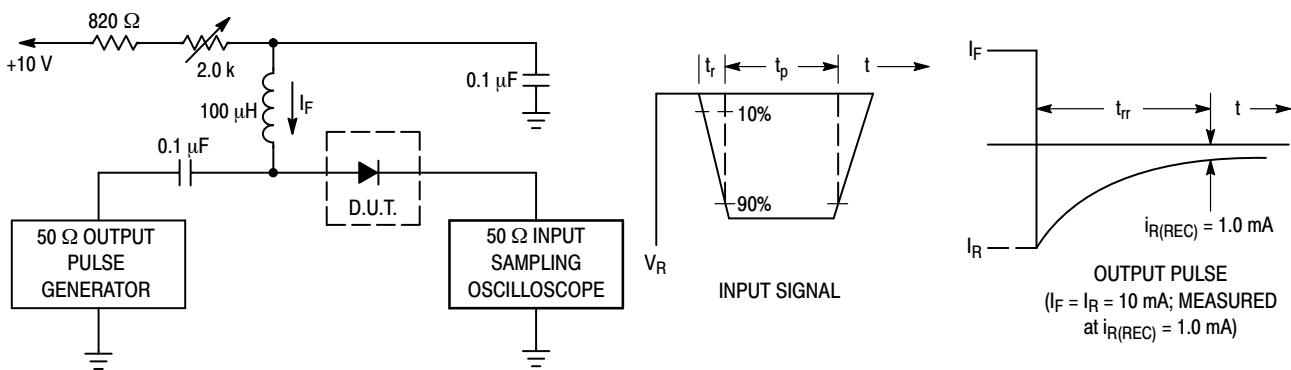


Figure 1. Recovery Time Equivalent Test Circuit

BAW56L, SBAW56L

Curves Applicable to Each Cathode

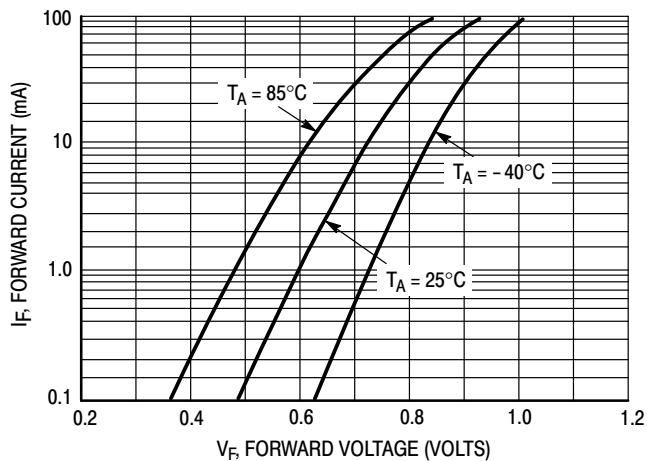


Figure 2. Forward Voltage

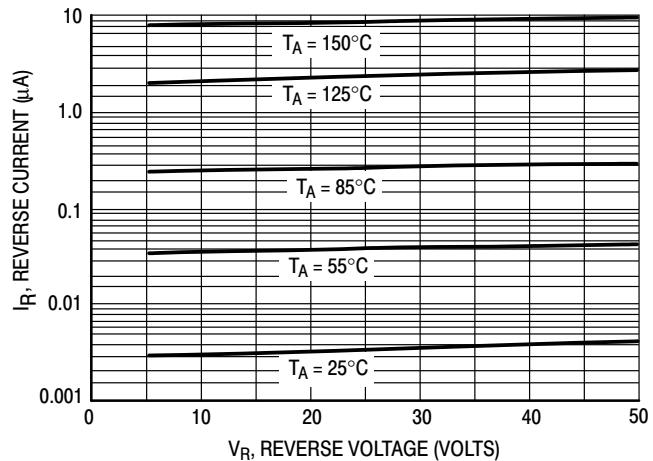


Figure 3. Leakage Current

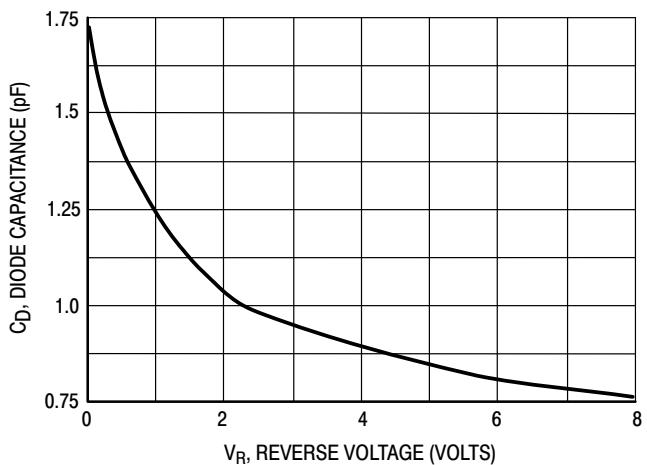


Figure 4. Capacitance

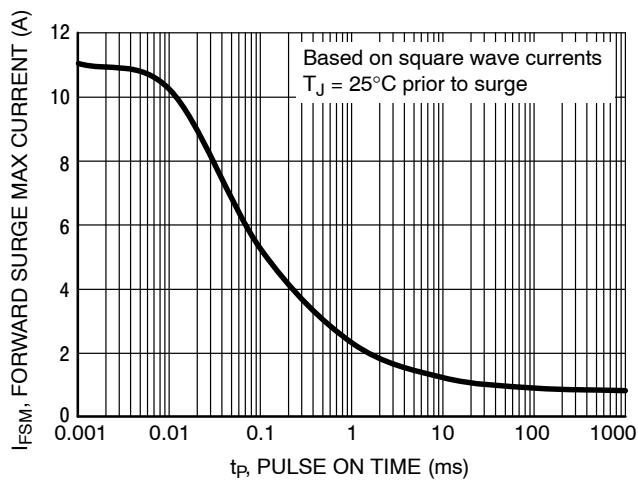
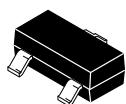


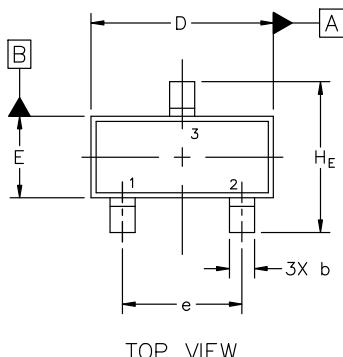
Figure 5. Forward Surge Current



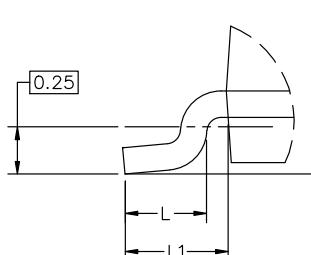
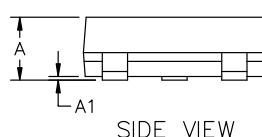
SCALE 4:1

SOT-23 (TO-236) 2.90x1.30x1.00 1.90P
CASE 318
ISSUE AU

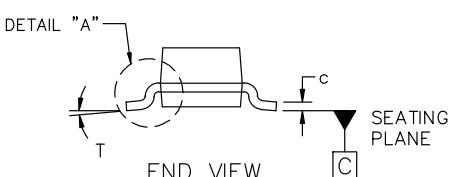
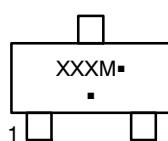
DATE 14 AUG 2024



TOP VIEW

DETAIL "A"
Scale 3:1

SIDE VIEW

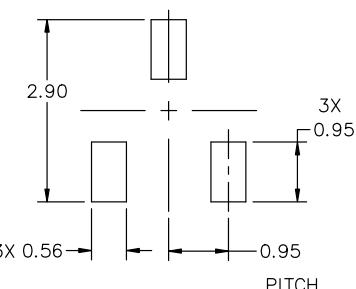
SEATING PLANE
CGENERIC
MARKING DIAGRAM*

XXX = Specific Device Code

M = Date Code

- = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

RECOMMENDED
MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.89	1.00	1.11
A1	0.01	0.06	0.10
b	0.37	0.44	0.50
c	0.08	0.14	0.20
D	2.80	2.90	3.04
E	1.20	1.30	1.40
e	1.78	1.90	2.04
L	0.30	0.43	0.55
L1	0.35	0.54	0.69
H_E	2.10	2.40	2.64
T	0°	---	10°

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSIONS: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

STYLES ON PAGE 2

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CASE 318

ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5:
CANCELLED

STYLE 6:
PIN 1. BASE
2. Emitter
3. Collector

STYLE 7:
PIN 1. Emitter
2. Base
3. Collector

STYLE 8:
PIN 1. Anode
2. No Connection
3. Cathode

STYLE 9:
PIN 1. Anode
2. Anode
3. Cathode

STYLE 10:
PIN 1. Drain
2. Source
3. Gate

STYLE 11:
PIN 1. Anode
2. Cathode
3. Cathode-Anode

STYLE 12:
PIN 1. Cathode
2. Cathode
3. Anode

STYLE 13:
PIN 1. Source
2. Drain
3. Gate

STYLE 14:
PIN 1. Cathode
2. Gate
3. Anode

STYLE 15:
PIN 1. Gate
2. Cathode
3. Anode

STYLE 16:
PIN 1. Anode
2. Cathode
3. Cathode

STYLE 17:
PIN 1. No Connection
2. Anode
3. Cathode

STYLE 18:
PIN 1. No Connection
2. Cathode
3. Anode

STYLE 19:
PIN 1. Cathode
2. Anode
3. Cathode-Anode

STYLE 20:
PIN 1. Cathode
2. Anode
3. Gate

STYLE 21:
PIN 1. Gate
2. Source
3. Drain

STYLE 22:
PIN 1. Return
2. Output
3. Input

STYLE 23:
PIN 1. Anode
2. Anode
3. Cathode

STYLE 24:
PIN 1. Gate
2. Drain
3. Source

STYLE 25:
PIN 1. Anode
2. Cathode
3. Gate

STYLE 26:
PIN 1. Cathode
2. Anode
3. No Connection

STYLE 27:
PIN 1. Cathode
2. Cathode
3. Cathode

STYLE 28:
PIN 1. Anode
2. Anode
3. Anode

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